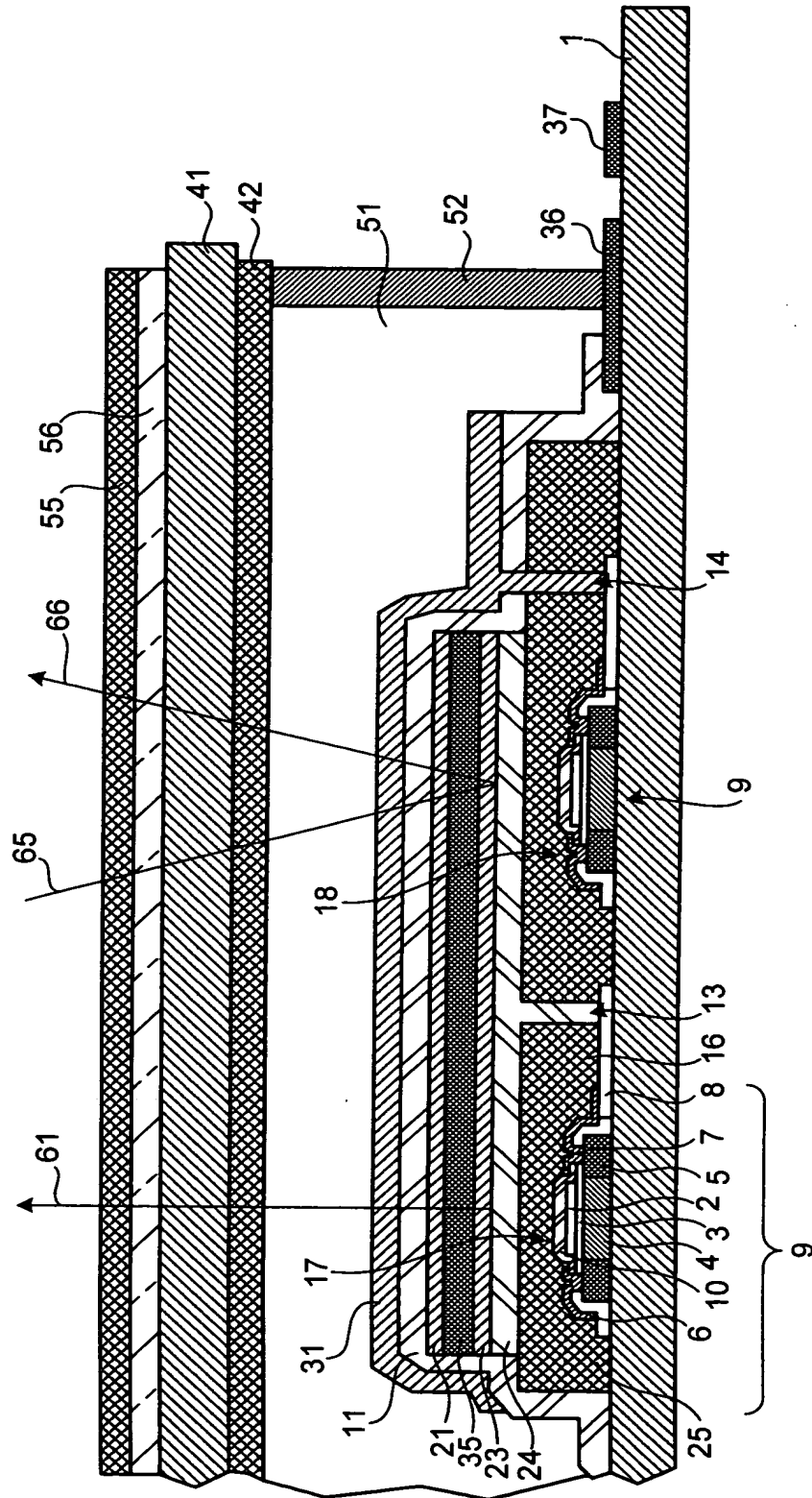


FIG. 1



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FIG.2

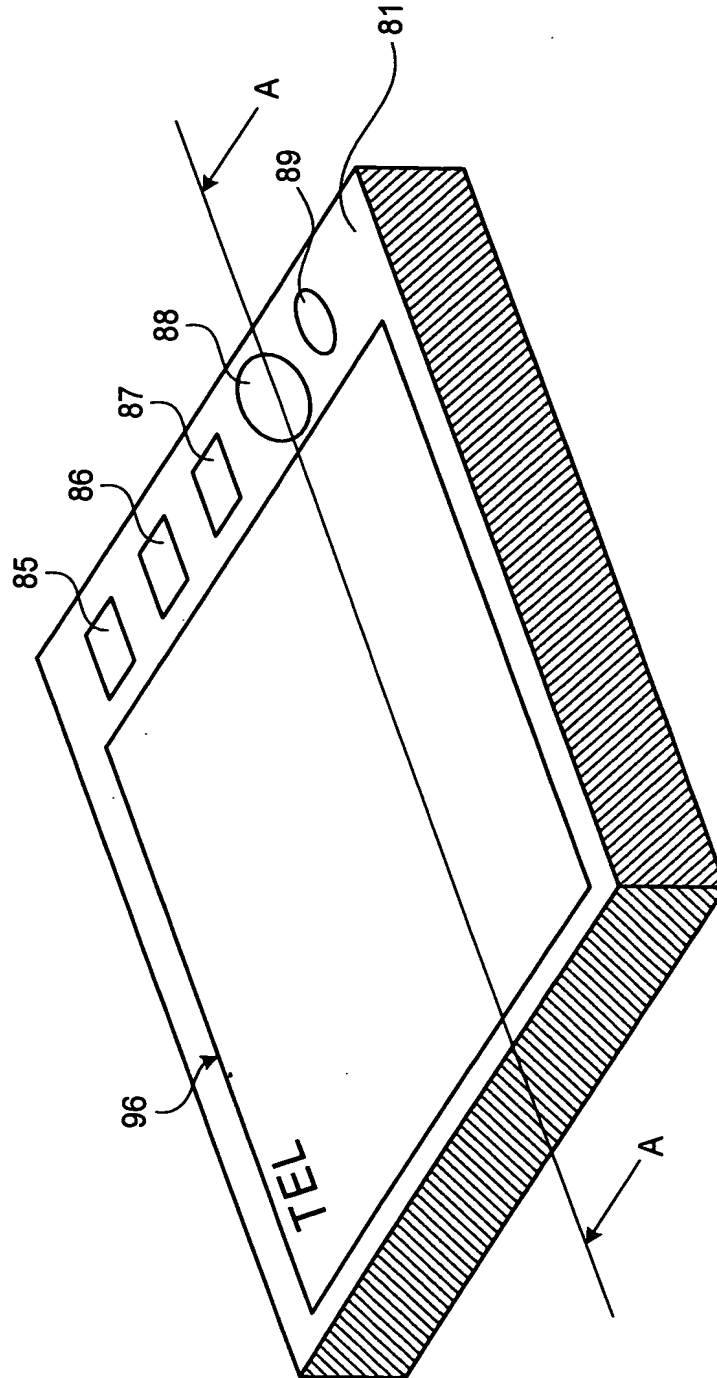


FIG.3

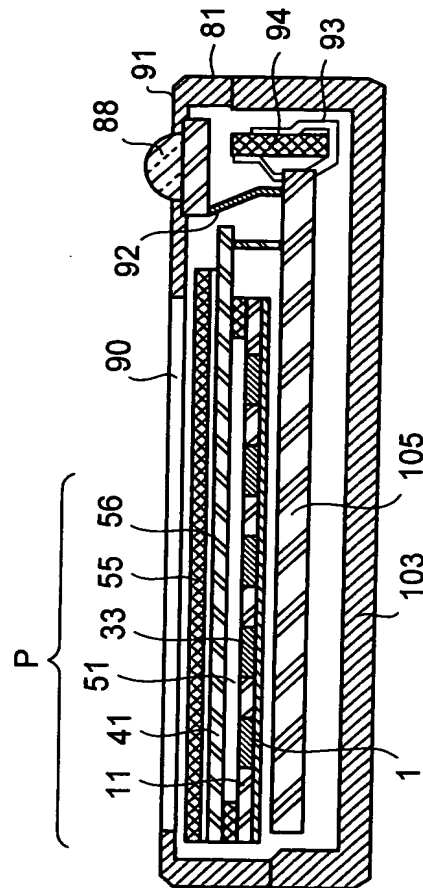
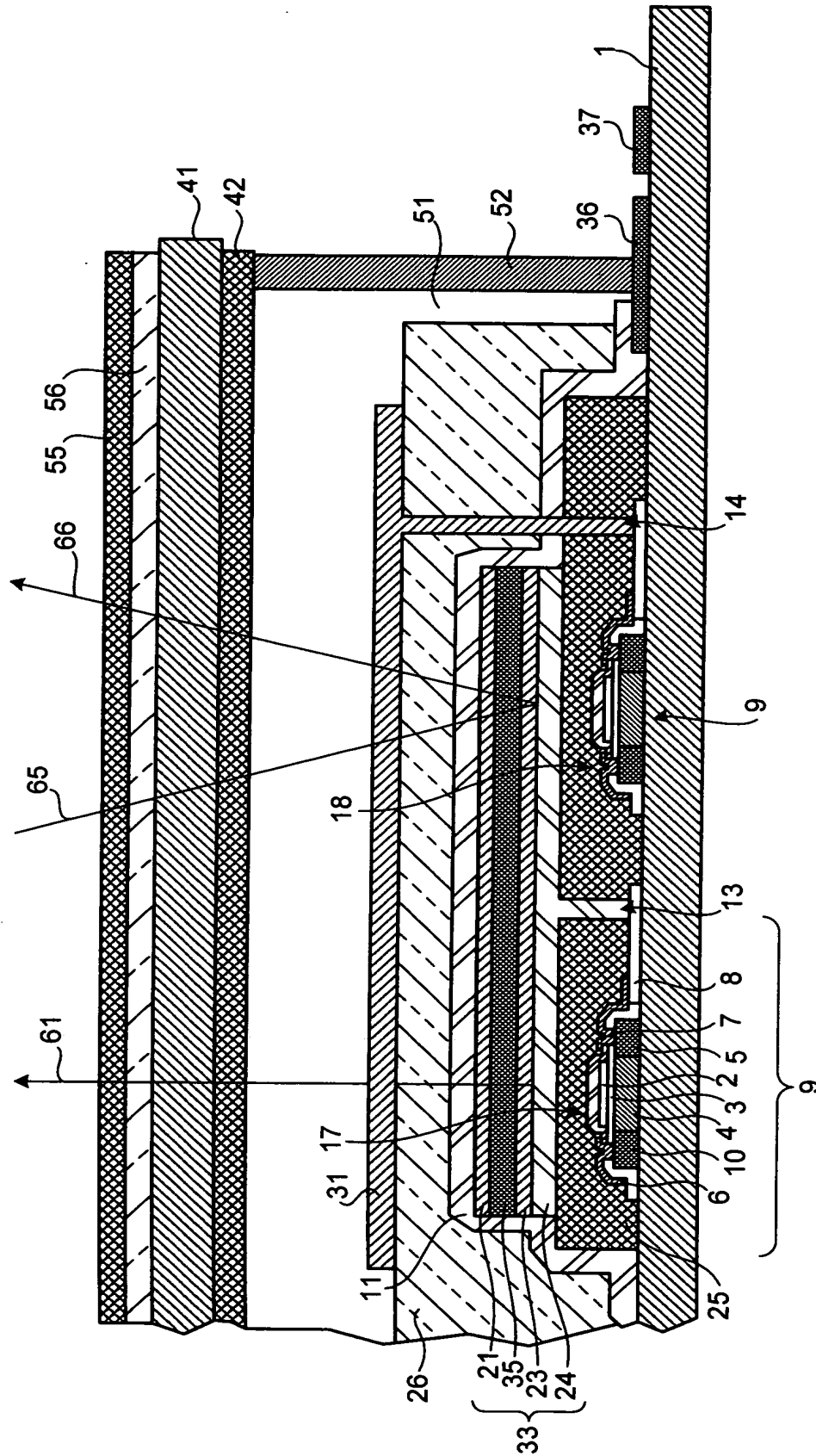


FIG. 5



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FIG. 9

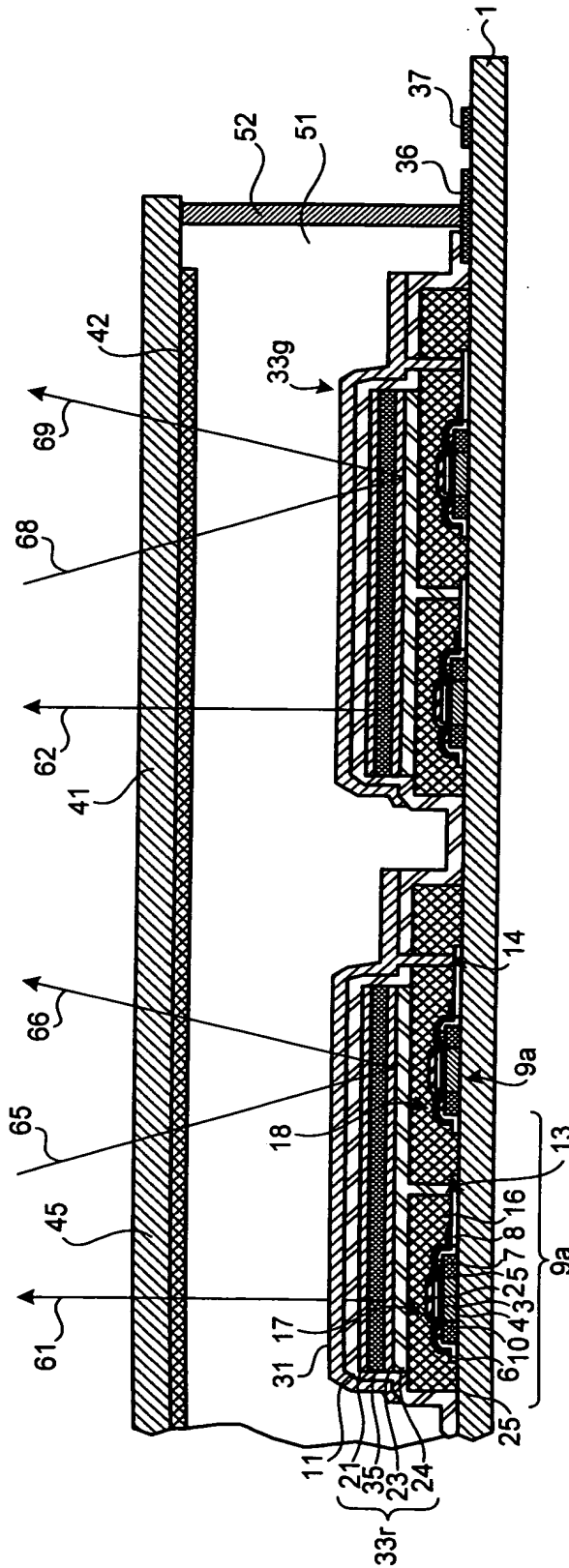
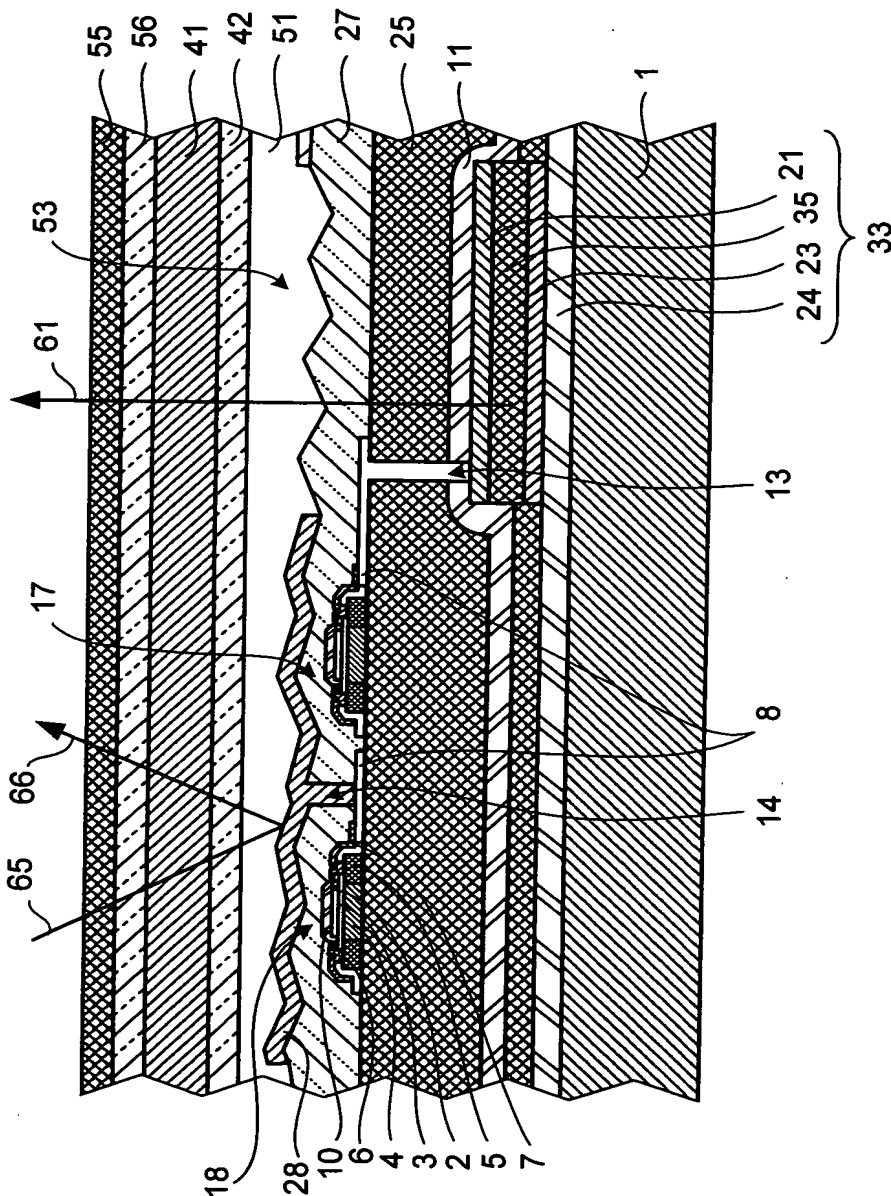


FIG.10



A detailed cross-sectional diagram of a semiconductor device. The device consists of several stacked layers. From top to bottom, the layers are labeled: 55 (cross-hatched), 56 (diagonal lines), 41 (horizontal lines), 42 (dotted), 51 (wavy surface), 27 (diagonal lines), 25 (cross-hatched), 11 (solid dark grey), 1 (diagonal lines), 59 (horizontal lines), and 58 (horizontal lines). On the left side, there is a complex structure with labels 18, 65, 66, and 17. In the center, there is a vertical stack of components labeled 28, 6, 4, 3, 2, 5, and 7. On the right side, there is a large rectangular component labeled 13, with arrows pointing to it from labels 61 and 33. Other labels include 8, 14, 21, 35, 23, and 24.

FIG. 12

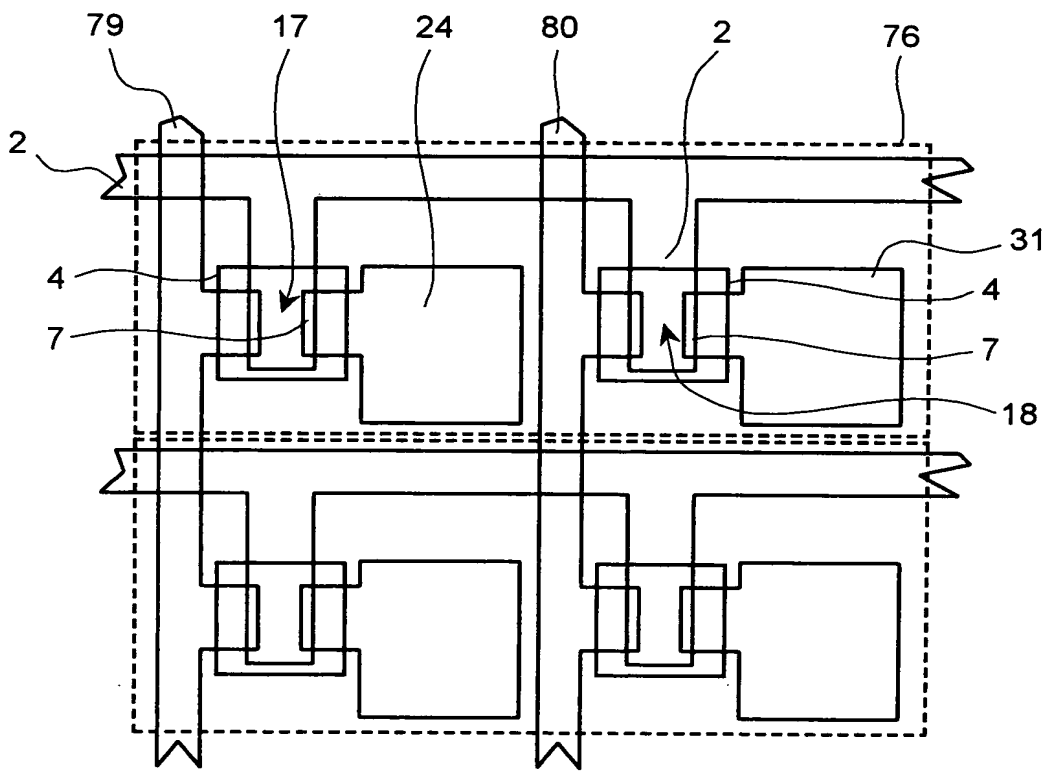


FIG. 13

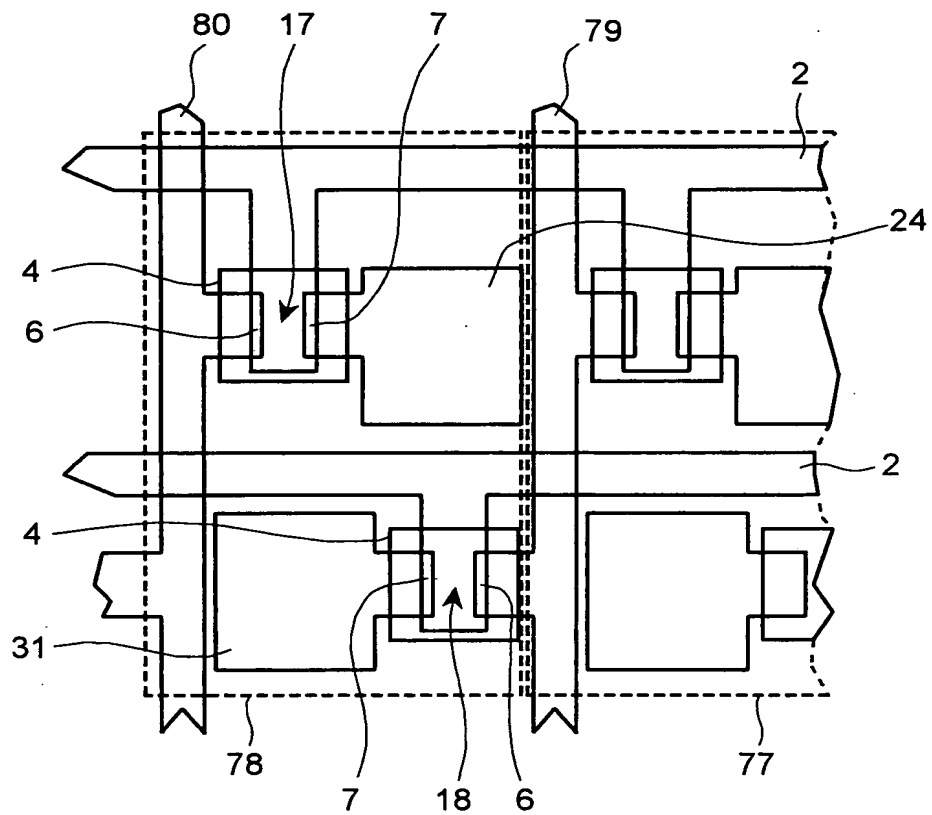
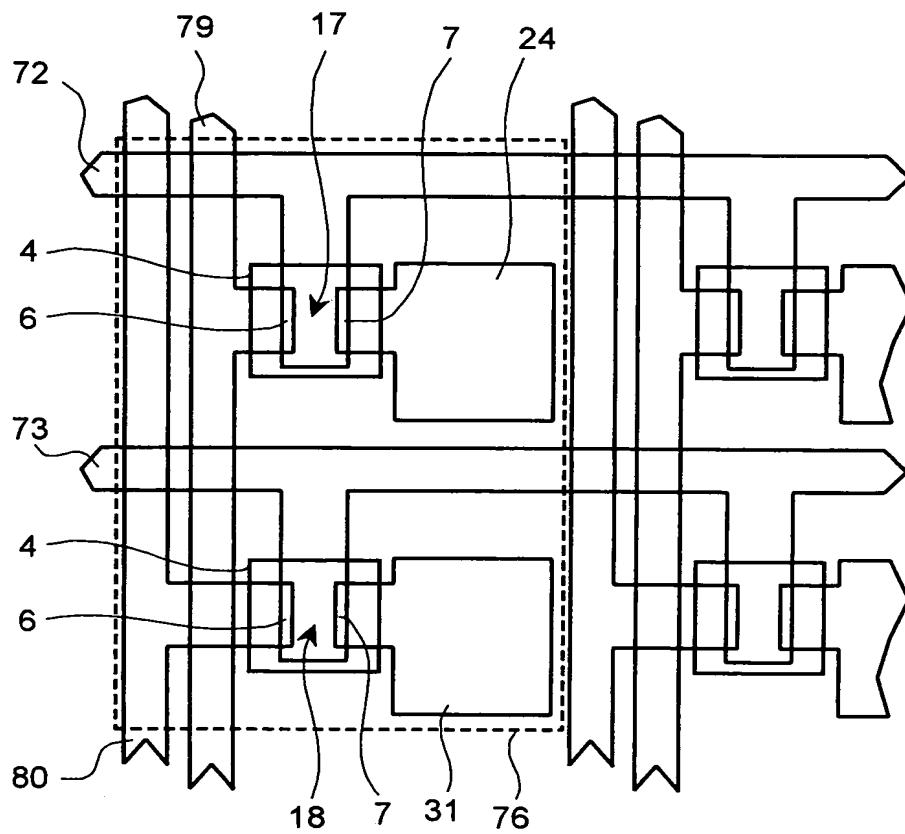
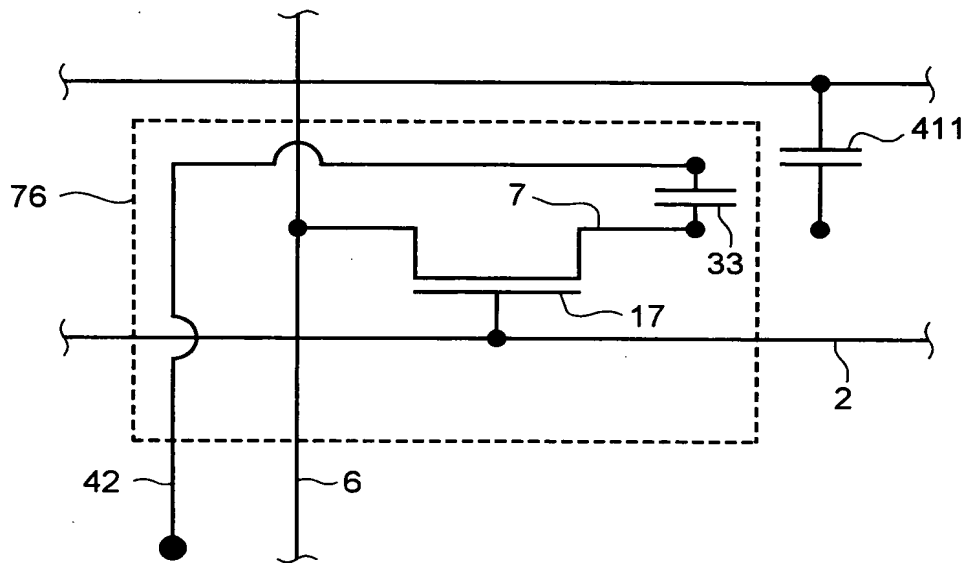


FIG. 14



The diagram shows a cross-section of a semiconductor device. At the top is a substrate labeled 1. Below it are several layers: layer 9, followed by a stack of layers numbered 6, 4, 2, 3, 5, 7, 8, and 13. Within or between these layers are various internal features, some indicated by arrows pointing to labels like 10, 25, 24, 22, 23, 35, 21, 31, 17, 42, 44, 41, 39, 56, 55, 45, 61, 66, and 65. A bracket groups layers 6 through 13 under the label 9. Another bracket groups layers 21 through 35 under the label 33. The bottom-most layer is labeled 11.

FIG. 17



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FIG. 18

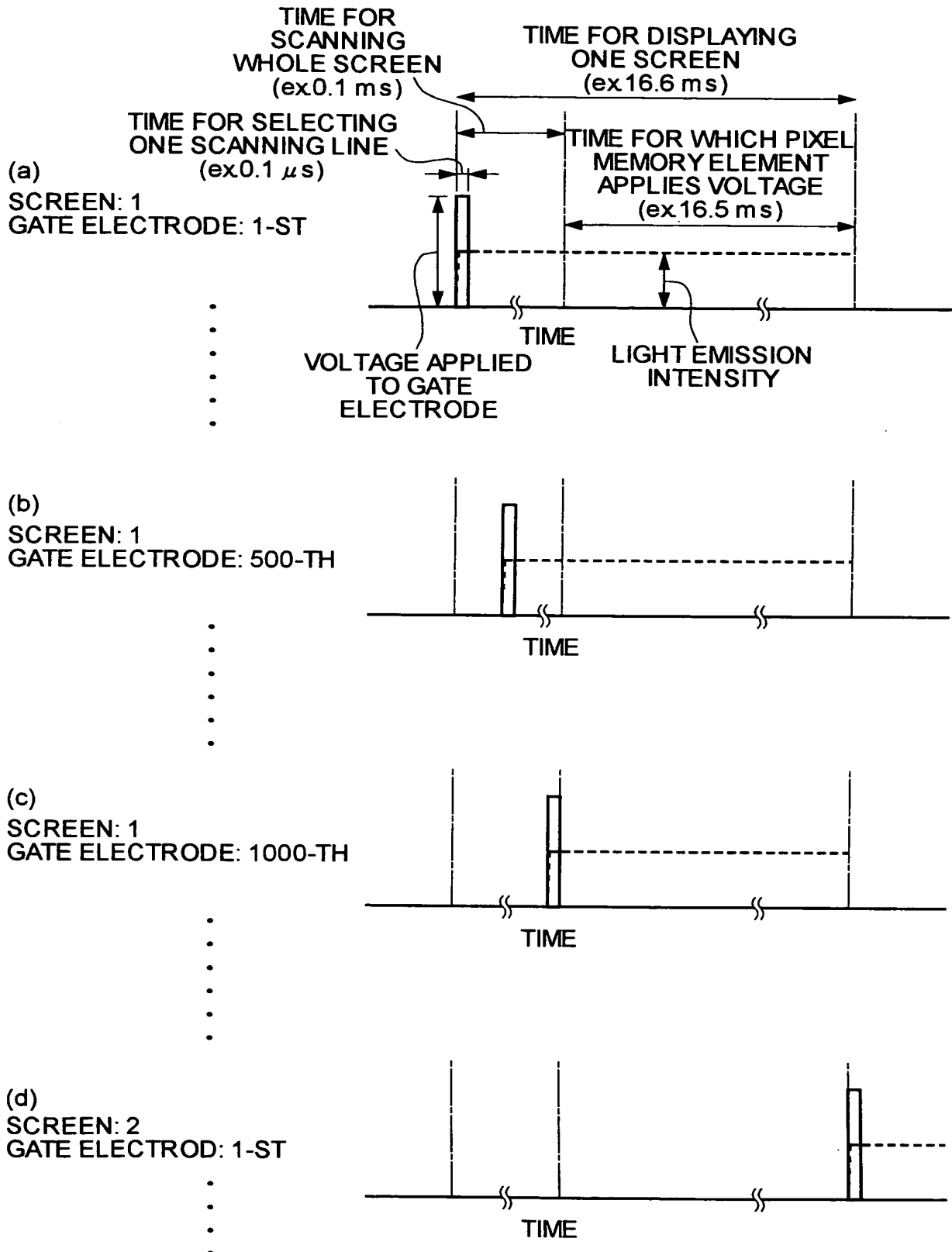
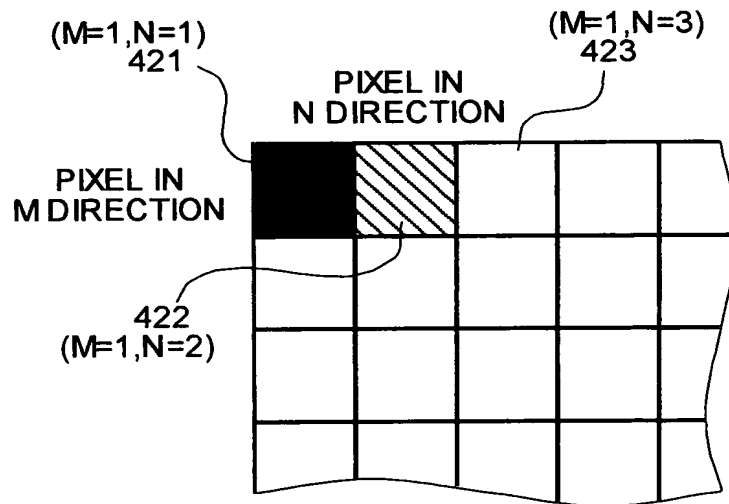


FIG. 19



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FIG.20

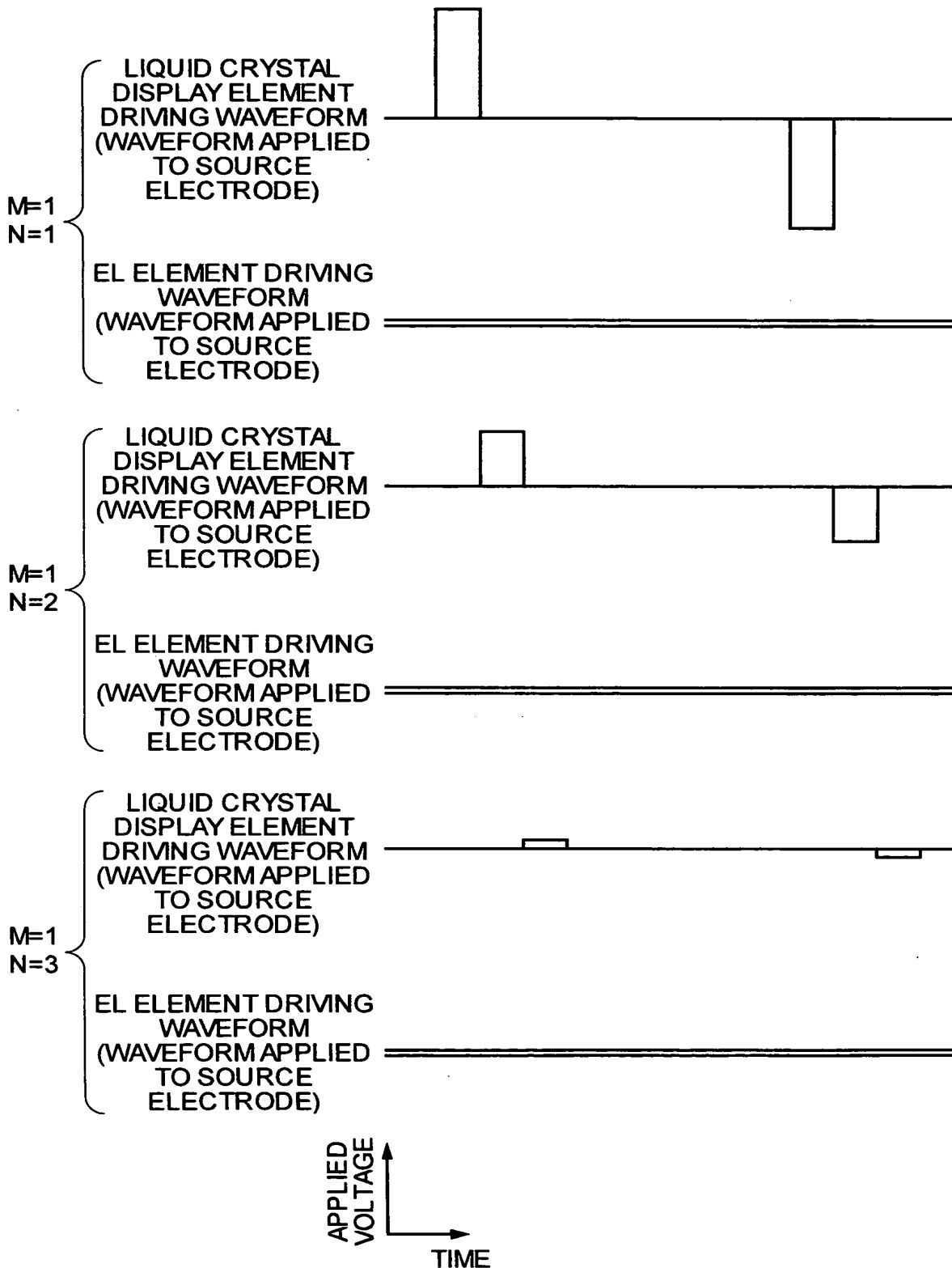
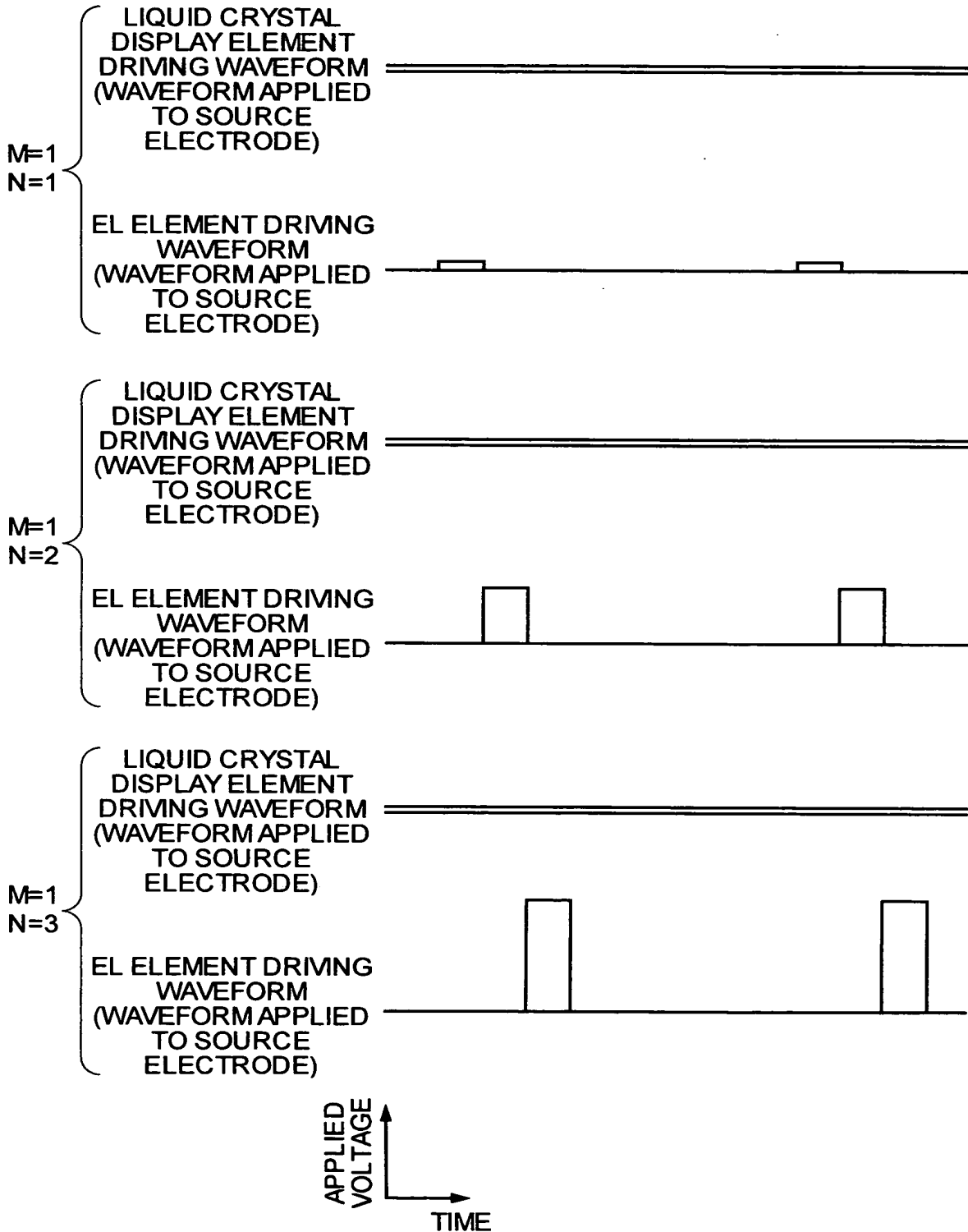


FIG.21



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FIG.22

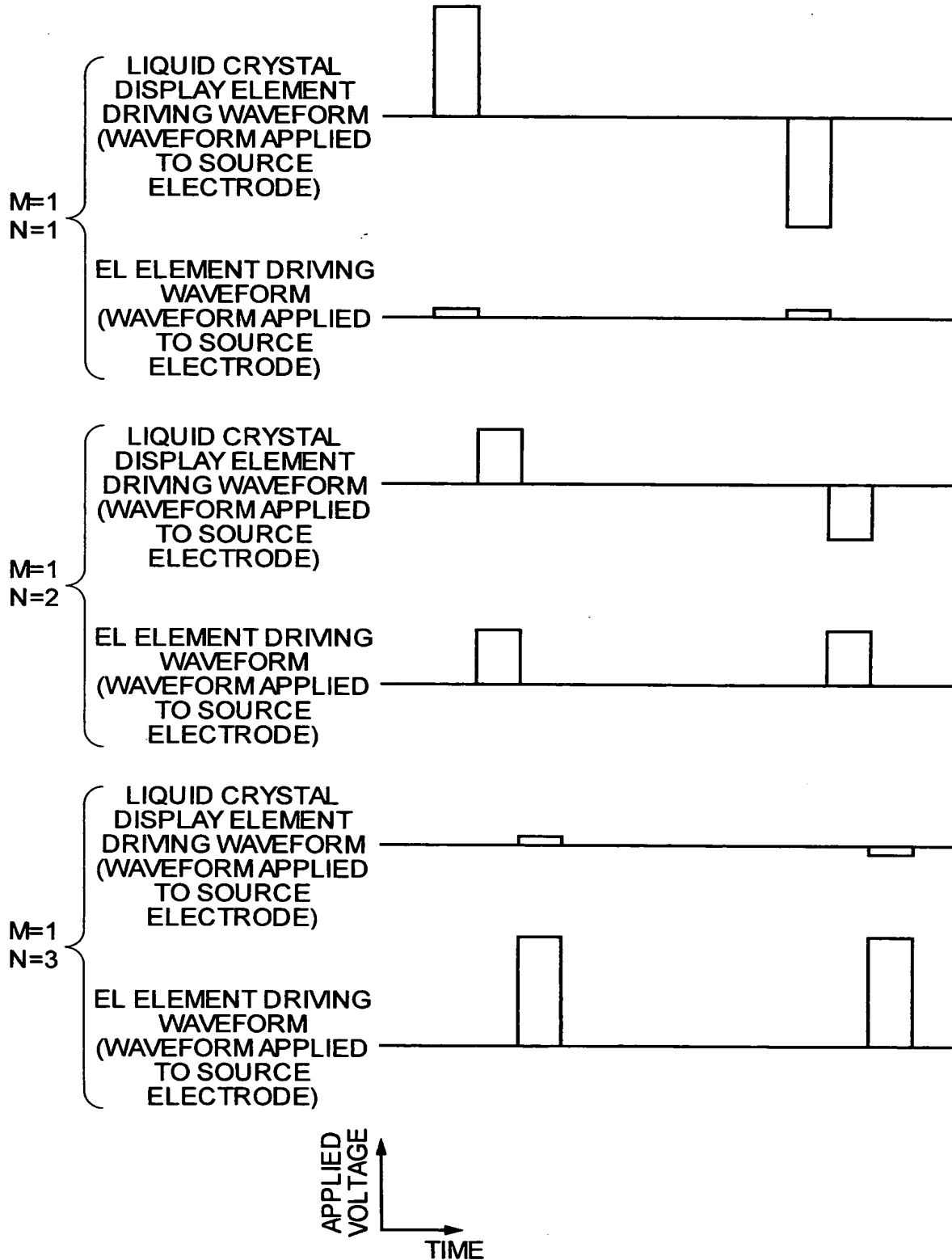


FIG.23

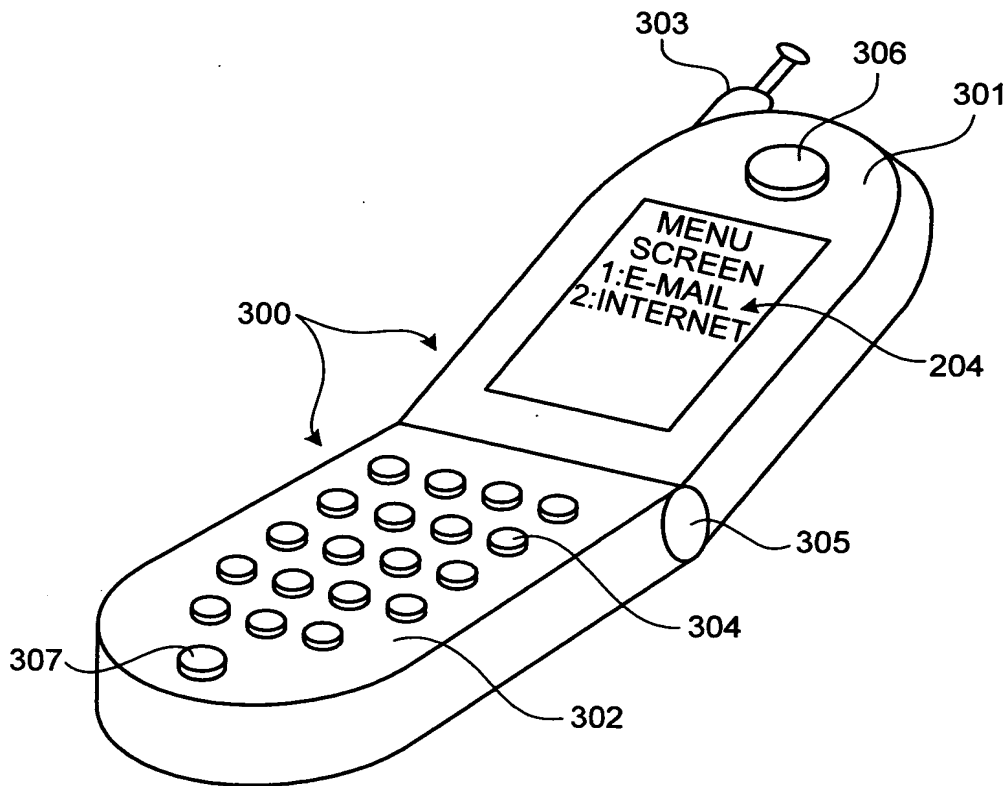


FIG.24

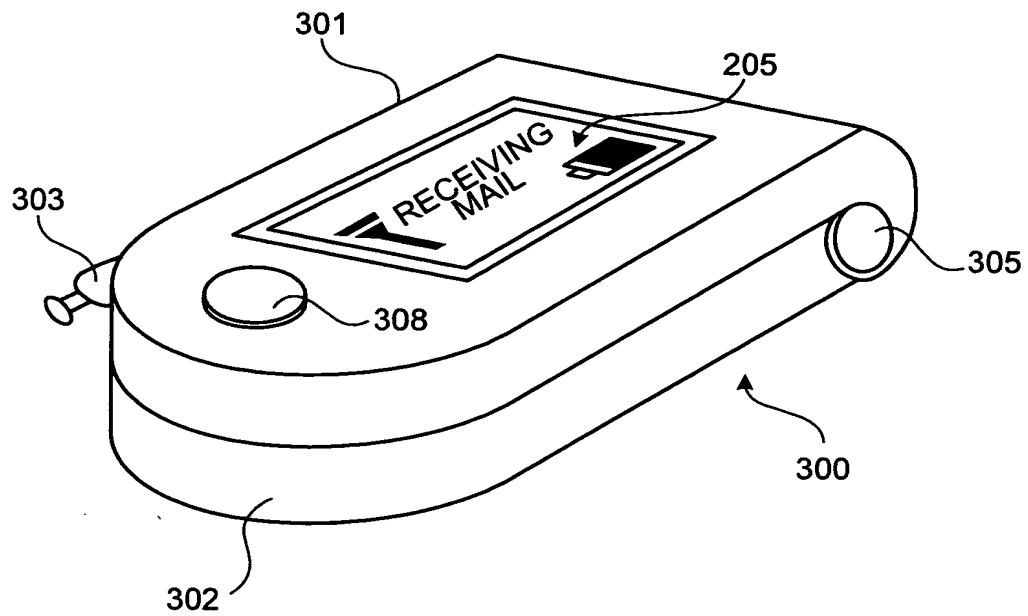


FIG. 25

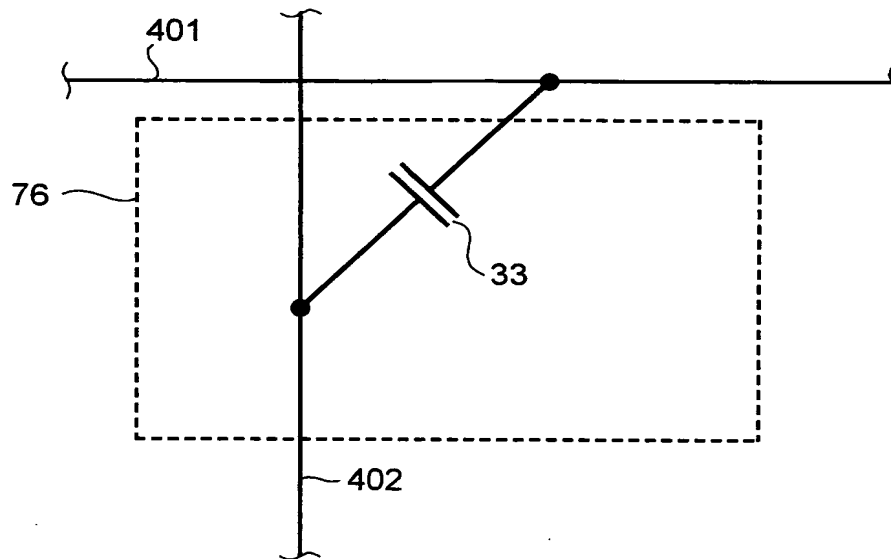


FIG.26

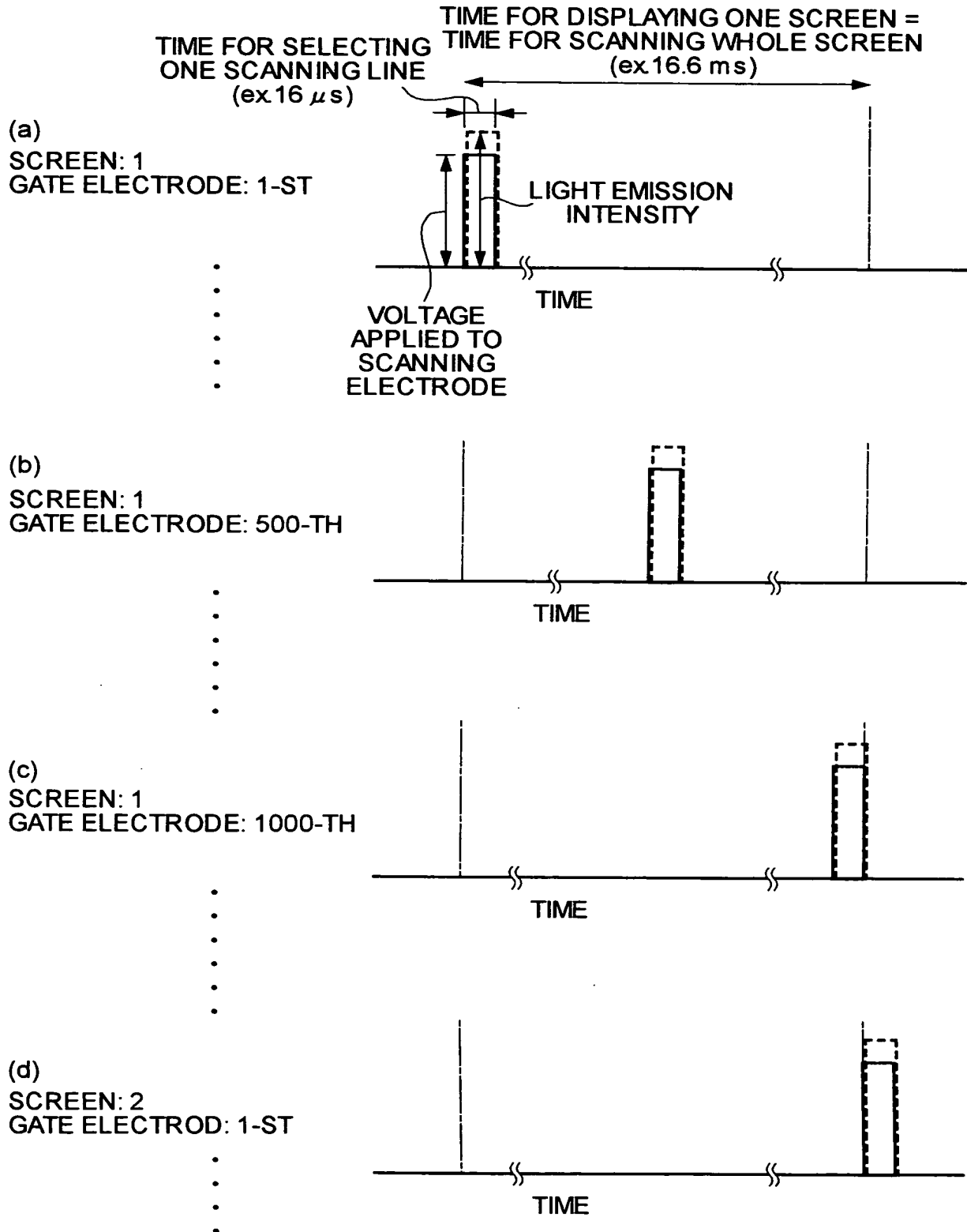


FIG.27

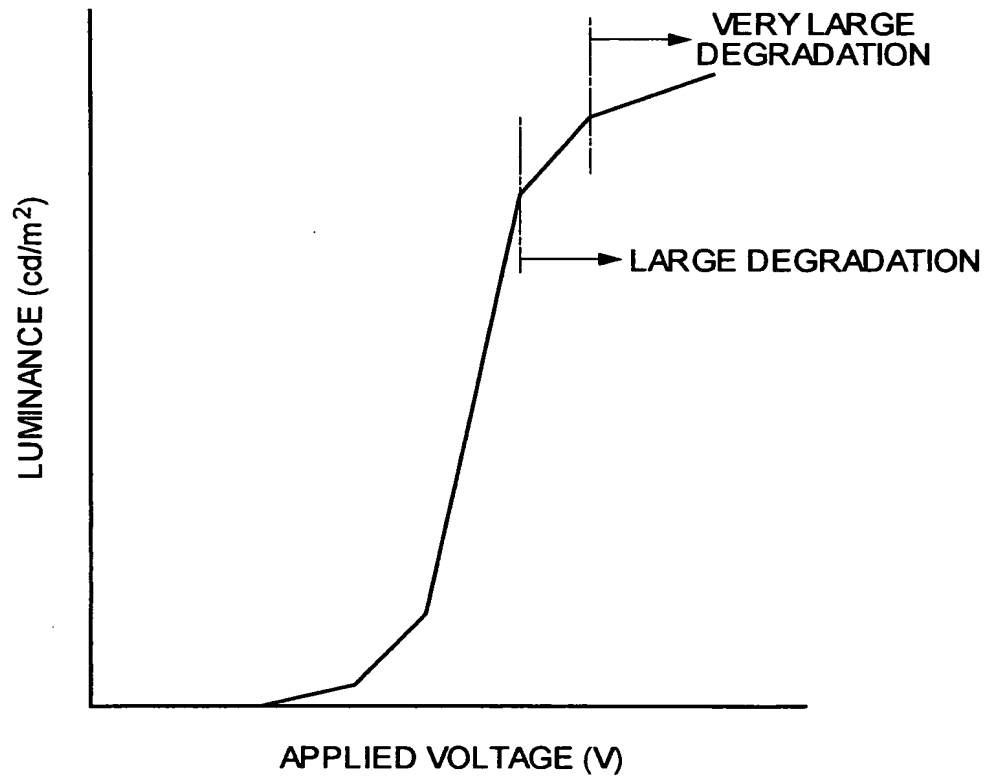


FIG. 28

